Silicon Carbide Schottky Diode

V_{RRM}	650V
$I_{F\ 135°C}$	

Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- AEC-Q101 qualified
- High-frequency operation
- Reduction of EMI

Typical ? piuctm] l T ! ȳ ib tm] ä uril v in v erter , electric car and charger.

Mechanical Data

- **Package**: TO-263
  Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- **Terminals**: Tin plated leads
- **Polarity**: As marked

■Maximum Ratings (T_C=25 Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D106520BXQG2
Reverse voltage (repetitive peak) @ T_j=25°C	V_{RRM}	V	650
Reverse voltage (Surge Peak) @ T_j=25°C	V_{RSM}	V	650
Reverse voltage (DC) @ T_j=25°C	V_{DC}	V	650
Continuous forward current @ T_c=25°C	I_F	A	48
Continuous forward current @ T_c=135°C			22
Continuous forward current @ T_c=140°C			20
Non-repetitive peak forward surge current @ T_c=25°C, tp=10ms, Half Sine Wave	I_{FSM}	A	160
Power Dissipation@ T_c=25°C	P_{TOT}	W	144
Power Dissipation@ T_c=110°C			62
i^2t Value@ Tc=25°C ,tp=10ms	$\int i^2dt$	A^2S	128
Operating junction and Storage temperature range	T_j ,T_{stg}	°C	-55 to +175

■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Typ.	Max.
Forward voltage drop	V_F	V	I_F=20A, T_j=25°C	1.35	1.55
			I_F=20A, T_j=175°C	1.75	-
Reverse leakage current	I_R	μA	V_R=650V, T_j=25°C	1	25
			V_R=650V, T_j=175°C	5	-
Total capacitive charge	Q_C	nC	V_R=400V, T_j=25°C , $QC=\int_0^{VR} C(V)dV$	62	-
Total capacitance	C	pF	V_R=0V, f=1MHZ	1157	-
			V_R=200V, f=1MHZ	115.6	-
			V_R=400V, f=1MHZ	107	-
Capacitance Stored Energy	E_C	μJ	V_R=400V	7.8	-

■Thermal Characteristics (T_a=25 Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	$R_{\theta J-C}$	°C /W	1.04

■Typical Characteristics

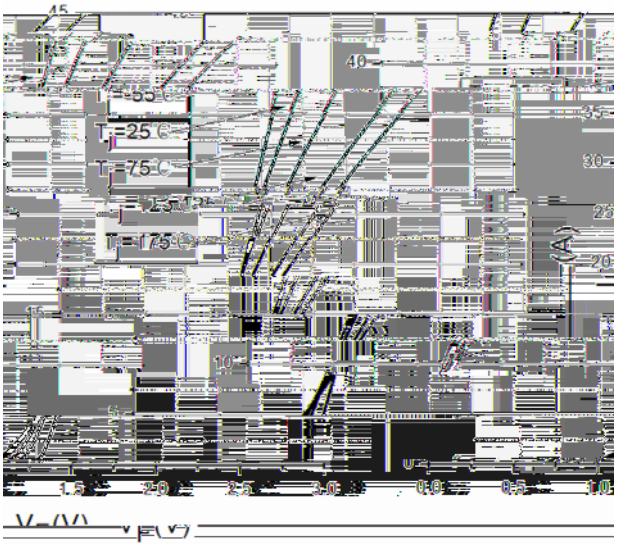

Figure 1. Forward Characteristics

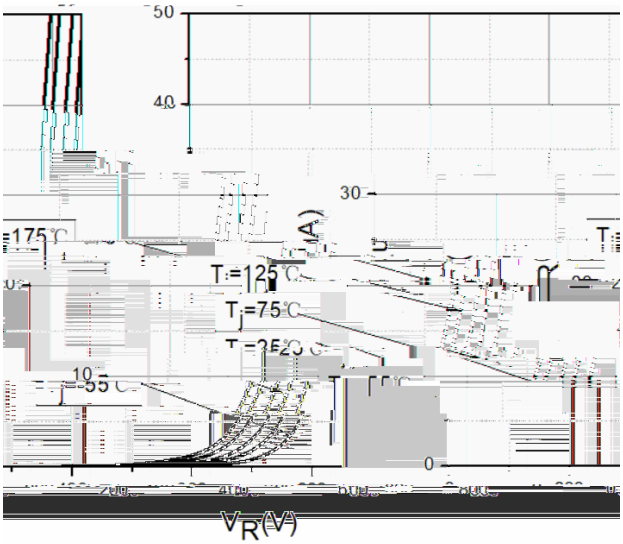

Figure2. Reverse Characteristic

Figure 3. Capacitance vs. Reverse Voltage

Figure 4. Total Capacitance Charge vs. Reverse Voltage

Figure 5. Capacitance Stored Energy

Figure 6. Power Derating

Figure 7. Current Derating

Figure 8. Transient Thermal Impedance

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